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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/747,768	12/29/2003	Il-seok Han	299256/39905	6484	
4743	7590 06/20/2005		EXAM	EXAMINER	
	L, GERSTEIN & BOR	WILSON, CH	WILSON, CHRISTIAN D		
SEARS TOW	KER DRIVE, SUITE 6300 /ER	ART UNIT	PAPER NUMBER		
CHICAGO,	IL 60606	2891	2891		
			DATE MAILED: 06/20/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Applicat	ion No.	Applicant(s)				
Office Action Summary		10/747,7	768	HAN, IL-SEOK				
		Examine	Г	Art Unit				
		Christian		2891				
: Period for I	The MAILING DATE of this commun Reply	ication appears on th	e cover sheet with the c	orrespondence add	Iress			
THE MA - Extension after SIX - If the period of the period	RTENED STATUTORY PERIOD FOR ALLING DATE OF THIS COMMUNIONS of time may be available under the provisions (6) MONTHS from the mailing date of this commit riod for reply specified above is less than thirty (3) riod for reply is specified above, the maximum state or reply within the set or extended period for reply y received by the Office later than three months a patent term adjustment. See 37 CFR 1.704(b).	CATION. of 37 CFR 1.136(a). In no enunication. O) days, a reply within the statutory period will apply and will, by statute, cause the ap	vent, however, may a reply be tim tutory minimum of thirty (30) days vill expire SIX (6) MONTHS from plication to become ABANDONEI	nely filed s will be considered timely, the mailing date of this cor O (35 U.S.C. § 133).				
Status								
1) 🗌 R	esponsive to communication(s) file	d on						
2a) TI	<u> </u>							
•	Since this application is in condition for allowance except for formal matters, prosecution as to the ments is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposition	of Claims							
4a 5)□ C 6)⊠ C 7)□ C	laim(s) 1-12 is/are pending in the analysis of the above claim(s) is/a laim(s) is/are allowed. laim(s) 1-12 is/are rejected. laim(s) is/are objected to. laim(s) are subject to restrict	re withdrawn from co						
· Application	n Papers							
10)⊠ Th Ap Re	te specification is objected to by the defending defendence of the	r 2003 is/are: a) ☐ action to the drawing(s) the correction is requi	be held in abeyance. See red if the drawing(s) is obj	e 37 CFR 1.85(a). lected to. See 37 CFI	R 1.121(d).			
Priority und	der 35 U.S.C. § 119							
12)⊠ Ac a)⊠ 1. 2. 3.	cknowledgment is made of a claim All b) Some * c) None of: Certified copies of the priority Copies of the certified copies application from the Internation the attached detailed Office action	documents have be documents have be of the priority docum nal Bureau (PCT Ru	en received. en received in Applicati ents have been receive lle 17.2(a)).	on No ed in this National S	Stage			
2) Notice o	f References Cited (PTO-892) f Draftsperson's Patent Drawing Review (P ion Disclosure Statement(s) (PTO-1449 or o(s)/Mail Date <u>12292003</u> .		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other: search histor	ate atent Application (PTO-	.152)			

DETAILED ACTION

Drawings

1. The drawings are objected to because the figures contain hand drawn figure and labels. Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Specification

2. The disclosure is objected to because of the following informalities: 35 U.S.C. 112, first paragraph, requires the specification to be written in "full, clear, concise, and exact terms." The specification is replete with terms which are not clear, concise and exact. The specification

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should be revised carefully in order to comply with 35 U.S.C. 112, first paragraph. Examples of some unclear, inexact or verbose terms used in the specification are: the use of the phrase "photo process" to describe ion implantation, etching, and oxide formation; describing the area key as having "a forward directional shape"; use of ungrammatical and poorly translated English.

Appropriate correction is required.

Claim Rejections - 35 USC § 112

- 3. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 4. Claims 1 12 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 5. The claims are generally narrative and indefinite, failing to conform with current U.S. practice. They appear to be a literal translation into English from a foreign document and are replete with grammatical and idiomatic errors. For example, claims 6 8 recite a selective etching process and an N-well photo process with no antecedent basis or clear understanding in English. Claim 7 recites a forward directional shape which is also indefinite.
- 6. Claim 1 recites the limitation "a silicon etching method". There is insufficient antecedent basis for this limitation in the claim since there is no previous claim of a silicon material.

 Further claim 11 recites a silicon etching which is indefinite for the same reason.

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7. Regarding claim 12, the phrase "such as" renders the claim indefinite because it is unclear whether the limitations following the phrase are part of the claimed invention. See MPEP § 2173.05(d).

Claim Rejections - 35 USC § 103

- 8. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 9. Claims 1 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yang in view of Cerny et al. and Lu.

Yang (US 5,422,286) teaches a method for manufacturing an alignment key comprising the steps of preparing a semiconductor substrate 12 divided into a scribe lane region and a main chip region [Figure 14], depositing a mask layer 43 on the substrate, forming an area key and a first align key by selectively etching the mask layer using an N-type ion implantation mask [Figure 7], performing an N-type ion implantation 46 on the region where the mask layer is removed, and forming a second align key 52 in the area key formed by the removal of the mask layer [Figure 9] by etching the silicon substrate [Figure 11]. Yang teaches an oxide mask layer in the second etching process so it would have been obvious to one of ordinary skill in the art to use an oxide mask in the first etching step since it provides an effective etching mask [column 4, lines 30-35]. Yang does not teach an N-well implantation and a P-well implantation. Cerny et al. (US 6,020,226) teaches a P-type implantation using the etching mask for an alignment mark

[Figure 2L]. Lu (US 5,814,552) teaches N and P well implantations and an oxide mask layer for forming an alignment mark [Figure 7]. It would have been obvious to one of ordinary skill in the art to use second etching mask for a second implantation since Cerny *et al.* teaches that this provides a more accurate alignment of the implantation while reducing the number of need mask layers. It also would have been obvious to one of ordinary skill in the art to use the well implants of Lu since Lu teaches that the wells provide a twin-well structure with improved electrical characteristics.

Regarding claim 2, Yang further teaches a dual etching process [Figure 12].

Regarding claim 3, Yang further teaches an oxide film with a thickness of 500-2000 Å [column 4, line 2].

Regarding claims 4 and 5, Yang further teaches removal of an RIE etching before ion implantation [Figure 7]. It would have been obvious to one of ordinary skill in the art to remove the photoresist over the implantation region before implantation since it is well known that RIE etching using a photolithography process removes the photoresist over the etched region.

Regarding claim 6, Yang further teaches forming a step region by selectively etching the scribe lane region [Figure 8].

Regarding claim 7, Yang further teaches a trench size of 1-20 μ m [column 3, line 58]. It would have been obvious to one of ordinary skill in the art to form a trench with a depth of 40 to 90 μ m in a thicker substrate layer since Yang teaches that the trench should have a depth of 5-20% of a substrate.

Regarding claims 8 and 9, Cerny et al. further teaches using the alignment marks for ion implantation [Figure 2L]. It would have been obvious to one of ordinary skill in the art to use

the alignments marks in Yang for the purposes of ion implantation since Cerny et al. teaches that this is a well known use of alignments marks for improved accuracy of the subsequent implantation.

Regarding claim 10, Yang further teaches silicon etching and oxide etching of the alignment pattern [Figure 12].

Regarding claim 11, Yang further teaches etching a second pattern with a depth of 1000 Å [column 4, lines 35-45].

Regarding claim 12, Yang further teaches a second alignment key with the same shape as the first alignment key [Figure 11].

Conclusion

- 10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The cited prior art teaches method of forming alignment keys.
- 11. A copy of the EAST search history is enclosed.
- 12. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christian Wilson whose telephone number is (571) 272-1886. The examiner can normally be reached on weekdays, 7:30 AM to 4 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on (571) 272-1722. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Christian Wilson, Ph.D.

Primary Examiner Art Unit 2891

CDW